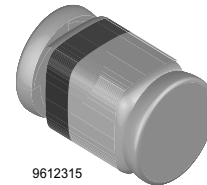


Small Signal Switching Diodes, High Voltage

Features

- Silicon Epitaxial Planar Diodes
- Saving space
- Hermetic sealed parts
- Fits onto SOD323 / SOT23 footprints
- Electrical data identical with the devices BAV100...BAV103 / BAV200...BAV203
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



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Applications

- General purposes

Mechanical Data

Case: MicroMELF Glass case

Weight: approx. 12 mg

Cathode Band Color: Black

Packaging Codes/Options:

TR3 / 10 k per 13" reel (8 mm tape), 10 k/box

TR / 2.5 k per 7" reel (8 mm tape), 12.5 k/box

Parts Table

Part	Type differentiation	Ordering code	Remarks
BAV300	$V_{RRM} = 60\text{ V}$	BAV300-TR3 or BAV300-TR	Tape and Reel
BAV301	$V_{RRM} = 120\text{ V}$	BAV301-TR3 or BAV301-TR	Tape and Reel
BAV302	$V_{RRM} = 200\text{ V}$	BAV302-TR3 or BAV302-TR	Tape and Reel
BAV303	$V_{RRM} = 250\text{ V}$	BAV303-TR3 or BAV303-TR	Tape and Reel

Absolute Maximum Ratings

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Value	Unit
Peak reverse voltage		BAV300	V_{RRM}	60	V
		BAV301	V_{RRM}	120	V
		BAV302	V_{RRM}	200	V
		BAV303	V_{RRM}	250	V
Reverse voltage		BAV300	V_R	50	V
		BAV301	V_R	100	V
		BAV302	V_R	150	V
		BAV303	V_R	200	V
Forward continuous current			I_F	250	mA
Peak forward surge current	$t_p = 1\text{ s}, T_j = 25\text{ }^{\circ}\text{C}$		I_{FSM}	1	A
Forward peak current	$f = 50\text{ Hz}$		I_{FM}	625	mA

Thermal Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Junction to ambient air	mounted on epoxy-glass hard tissue, Fig. 4 35 μm copper clad, 0.9 mm^2 copper area per electrode	R_{thJA}	500	K/W
Junction temperature		T_j	175	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	- 65 to + 175	$^{\circ}\text{C}$

Electrical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Forward voltage	$I_F = 100\text{ mA}$		V_F			1000	mV
Reverse current	$V_R = 50\text{ V}$	BAV300	I_R			100	nA
	$V_R = 100\text{ V}$	BAV301	I_R			100	nA
	$V_R = 150\text{ V}$	BAV302	I_R			100	nA
	$V_R = 200\text{ V}$	BAV303	I_R			100	nA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 50\text{ V}$	BAV300	I_R			15	μA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 100\text{ V}$	BAV301	I_R			15	μA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 150\text{ V}$	BAV302	I_R			15	μA
	$T_j = 100\text{ }^{\circ}\text{C}$, $V_R = 200\text{ V}$	BAV303	I_R			15	μA
Breakdown voltage	$I_R = 100\text{ }\mu\text{A}$, $t_p/T = 0.01$, $t_p = 0.3\text{ ms}$	BAV300	$V_{(BR)}$	60			V
	$I_R = 100\text{ }\mu\text{A}$, $t_p/T = 0.01$, $t_p = 0.3\text{ ms}$	BAV301	$V_{(BR)}$	120			V
		BAV302	$V_{(BR)}$	200			V
		BAV303	$V_{(BR)}$	250			V
Diode capacitance	$V_R = 0$, $f = 1\text{ MHz}$		C_D		1.5		pF
Differential forward resistance	$I_F = 10\text{ mA}$		r_f		5		Ω
Reverse recovery time	$I_F = I_R = 30\text{ mA}$, $i_R = 3\text{ mA}$, $R_L = 100\text{ }\Omega$		t_{rr}			50	ns

Typical Characteristics

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

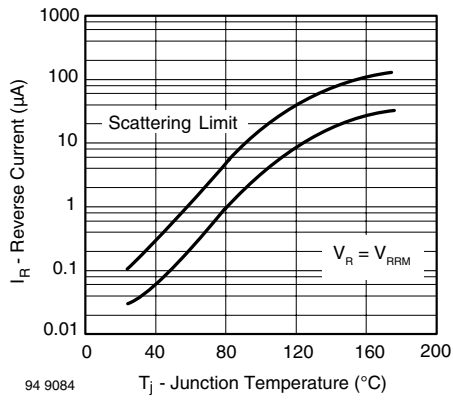


Figure 1. Reverse Current vs. Junction Temperature

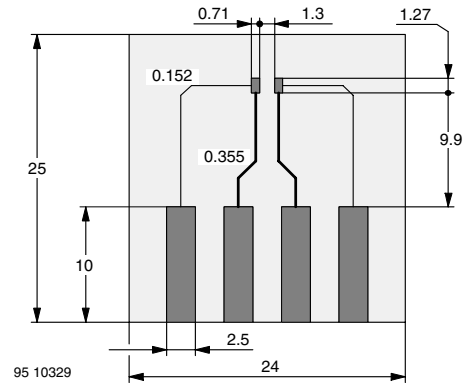


Figure 4. Board for R_{thJA} definition (in mm)

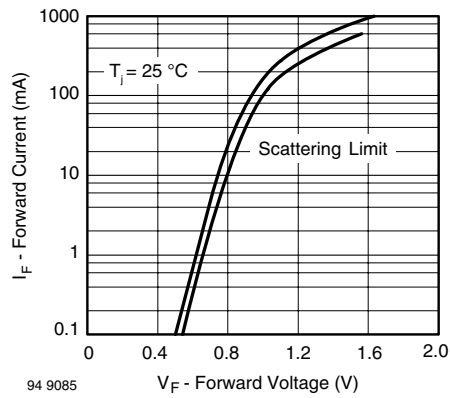


Figure 2. Forward Current vs. Forward Voltage

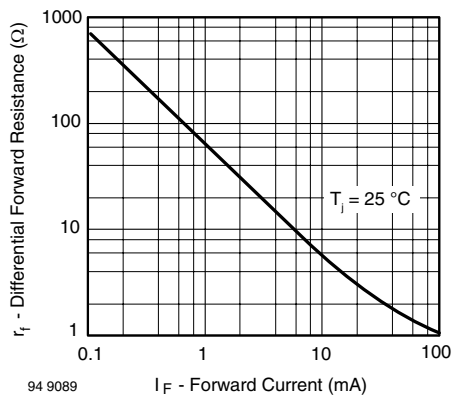
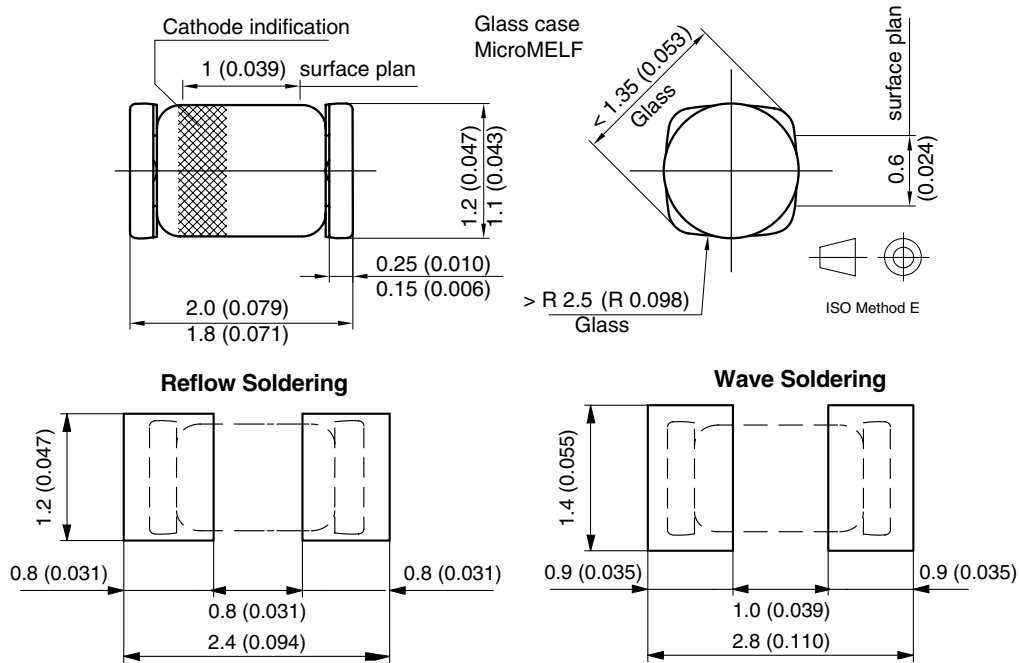


Figure 3. Differential Forward Resistance vs. Forward Current

Package Dimensions in mm (Inches)



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